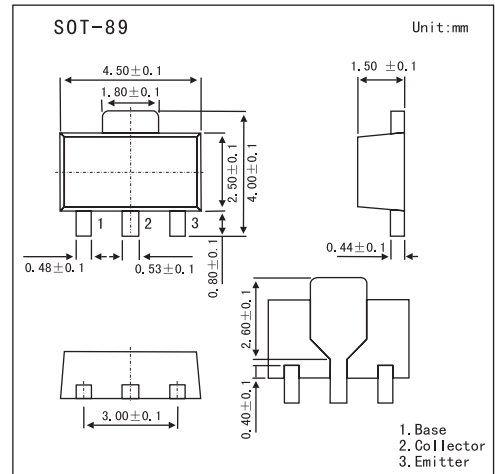


2SD1418

Features

- Low frequency power amplifier.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CB0}	120	V
Collector to emitter voltage	V _{CEO}	80	V
Emitter to base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Peak collector current	I _{CP} *1	2	A
Collector power dissipation	P _C *2	1	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

*1. PW ≤ 10 ms; d ≤ 0.02.

*2. Value on the alumina ceramic board (12.5 X 20 X 0.7 mm)

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10 μA, I _E = 0	120			V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1 mA, R _{BE} = ∞	80			V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10 μA, I _C = 0	5			V
Collector cutoff current	I _{CBO}	V _{CB} = 100 V, I _E = 0			10	μA
DC current transfer ratio	h _{FE}	V _{CE} = 5 V, I _C = 150 mA	60		320	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 500 mA, I _B = 50 mA			1	V
Base to emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 150 mA			1.5	V
Gain bandwidth product	f _T	V _{CE} = 5 V, I _C = 150 mA		140		MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz		12		pF

hFE Classification

Marking	D		
	A	B	C
hFE	60~120	100~200	160~320